Stacia Keller

List of Publications by Year
in descending order

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251	8,613	50170 46	60497 81
papers	citations	h-index	g-index

253	253	253	5496
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Origin of defect-insensitive emission probability in In-containing (Al,In,Ga)N alloy semiconductors. Nature Materials, 2006, 5, 810-816.	13.3	625
2	Development of gallium-nitride-based light-emitting diodes (LEDs) and laser diodes for energy-efficient lighting and displays. Acta Materialia, 2013, 61, 945-951.	3.8	352
3	Growth of Fe doped semi-insulating GaN by metalorganic chemical vapor deposition. Applied Physics Letters, 2002, 81, 439-441.	1.5	326
4	Demonstration of Nonpolarm-Plane InGaN/GaN Light-Emitting Diodes on Free-Standingm-Plane GaN Substrates. Japanese Journal of Applied Physics, 2005, 44, L173-L175.	0.8	200
5	High internal and external quantum efficiency InGaN/GaN solar cells. Applied Physics Letters, 2011, 98, .	1.5	195
6	Crystallographic orientation dependence of dopant and impurity incorporation in GaN films grown by metalorganic chemical vapor deposition. Journal of Crystal Growth, 2009, 311, 3817-3823.	0.7	192
7	Polarization effects in AlGaN/GaN and GaN/AlGaN/GaN heterostructures. Journal of Applied Physics, 2003, 93, 10114-10118.	1.1	188
8	N-polar GaN epitaxy and high electron mobility transistors. Semiconductor Science and Technology, 2013, 28, 074009.	1.0	172
9	Realization of wide electron slabs by polarization bulk doping in graded IIIâ€“V nitride semiconductor alloys. Applied Physics Letters, 2002, 81, 4395-4397.	1.5	163
10	Recent progress in metal-organic chemical vapor deposition of $left(000ar{1} ight)$ N-polar group-III nitrides. Semiconductor Science and Technology, 2014, 29, 113001.	1.0	163
11	Memory Effect and Redistribution of Mg into Sequentially Regrown GaN Layer by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2003, 42, 50-53.	0.8	158
12	Demonstration of Constant 8 W/mm Power Density at 10, 30, and 94 GHz in State-of-the-Art Millimeter-Wave N-Polar GaN MISHEMTs. IEEE Transactions on Electron Devices, 2018, 65, 45-50.	1.6	153
13	Infrared and Raman-scattering studies in single-crystalline GaN nanowires. Chemical Physics Letters, 2001, 345, 245-251.	1.2	152
14	In Situ <italic>O</italic>xide, <italic>G</italic>aN Interlayer-Based Vertical Trench MOS<italic>FET</italic> (<italic>OG-FET</italic>) on Bulk GaN substrates. IEEE Electron Device Letters, 2017, 38, 353-355.	2.2	130
15	Ultralow nonalloyed Ohmic contact resistance to self aligned N-polar GaN high electron mobility transistors by In(Ga)N regrowth. Applied Physics Letters, 2010, 96, .	1.5	122
16	Polarity in GaN and ZnO: Theory, measurement, growth, and devices. Applied Physics Reviews, 2016, 3, .	5.5	105
17	Two-photon absorption study of GaN. Applied Physics Letters, 2000, 76, 439-441.	1.5	97
18	Demonstration of ultra-small (<10 Î¼m) 632 nm red InGaN micro-LEDs with useful on-wafer external quantum efficiency (>0.2%) for mini-displays. Applied Physics Express, 2021, 14, 011004.	1.1	96

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19	Charge control and mobility in AlGaN/GaN transistors: Experimental and theoretical studies. Journal of Applied Physics, 2000, 87, 7981-7987.	1.1	89
20	Radiative and nonradiative processes in strain-free AlxGa1â˜xN films studied by time-resolved photoluminescence and positron annihilation techniques. Journal of Applied Physics, 2004, 95, 2495-2504.	1.1	88
21	Design, fabrication, and performance analysis of GaN vertical electron transistors with a buried p/n junction. Applied Physics Letters, 2015, 106, .	1.5	81
22	Normally OFF Trench CAVET With Active Mg-Doped GaN as Current Blocking Layer. IEEE Transactions on Electron Devices, 2017, 64, 805-808.	1.6	76
23	N-Polar GaN Cap MISHEMT With Record Power Density Exceeding 6.5 W/mm at 94 GHz. IEEE Electron Device Letters, 2017, 38, 359-362.	2.2	74
24	W-Band Power Performance of SiN-Passivated N-Polar GaN Deep Recess HEMTs. IEEE Electron Device Letters, 2020, 41, 349-352.	2.2	74
25	880 V/$2.7~ext{m}Omegacdotext{cm}^{ext{2}}$ MIS Gate Trench CAVET on Bulk GaN Substrates. IEEE Electron Device Letters, 2018, 39, 863-865.	2.2	73
26	Metalorganic chemical vapor deposition of group III nitridesâ€”a discussion of critical issues. Journal of Crystal Growth, 2003, 248, 479-486.	0.7	72
27	High conductivity modulation doped AlGaN/GaN multiple channel heterostructures. Journal of Applied Physics, 2003, 94, 5321.	1.1	72
28	N-Polar GaN HEMTs Exhibiting Record Breakdown Voltage Over 2000 V and Low Dynamic On-Resistance. IEEE Electron Device Letters, 2018, 39, 1014-1017.	2.2	70
29	Nonpolarm-Plane Blue-Light-Emitting Diode Lamps with Output Power of 23.5 mW under Pulsed Operation. Japanese Journal of Applied Physics, 2006, 45, 739-741.	0.8	68
30	Effect of doping and polarization on carrier collection in InGaN quantum well solar cells. Applied Physics Letters, 2011, 98, .	1.5	68
31	Low nonalloyed Ohmic contact resistance to nitride high electron mobility transistors using N-face growth. Applied Physics Letters, 2007, 91, .	1.5	67
32	Preparation of indium nitride micro- and nanostructures by ammonolysis of indium oxide. Journal of Materials Chemistry, 2004, 14, 637.	6.7	65
33	Scanning second-harmonic/third-harmonic generation microscopy of gallium nitride. Applied Physics Letters, 2000, 77, 2331-2333.	1.5	63
34	OG-FET: An In-Situ ${O}$ xide, ${G}$ aN Interlayer-Based Vertical Trench MOSFET. IEEE Electron Device Letters, 2016, 37, 1601-1604.	2.2	63
35	V-Gate GaN HEMTs for X-Band Power Applications. IEEE Electron Device Letters, 2008, 29, 974-976.	2.2	62
36	Atom probe analysis of AlN interlayers in AlGaN/AlN/GaN heterostructures. Applied Physics Letters, 2013, 102, .	1.5	62

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37	High-transconductance self-aligned AlGaN/GaN modulation-doped field-effect transistors with regrown ohmic contacts. Applied Physics Letters, 1998, 73, 3147-3149.	1.5	60
38	Effect of quantum well cap layer thickness on the microstructure and performance of InGaN/GaN solar cells. Applied Physics Letters, 2012, 100, .	1.5	53
39	Demonstrating >1.4 kV OG-FET performance with a novel double field-plated geometry and the successful scaling of large-area devices. , 2017, , .		53
40	Spiral Growth of InGaN Nanoscale Islands on GaN. Japanese Journal of Applied Physics, 1998, 37, L431-L434.	0.8	52
41	Growth study and impurity characterization of Al In1â^'N grown by metal organic chemical vapor deposition. Journal of Crystal Growth, 2011, 324, 163-167.	0.7	52
42	Large-Area <italic>In-Situ</italic> Oxide, GaN Interlayer-Based Vertical Trench MOSFET (OG-FET). IEEE Electron Device Letters, 2018, 39, 711-714.	2.2	52
43	Effect of the Nucleation Conditions on the Polarity of AlN and GaN Films Grown on C-face 6H-SiC. Japanese Journal of Applied Physics, 2006, 45, L322-L325.	0.8	51
44	Design of High-Aspect-Ratio T-Gates on N-Polar GaN/AlGaN MIS-HEMTs for High f_{max}. IEEE Electron Device Letters, 2012, 33, 785-787.	2.2	51
45	Mass transport regrowth of GaN for ohmic contacts to AlGaN/GaN. Applied Physics Letters, 2001, 78, 2876-2878.	1.5	49
46	Comparing electrical performance of GaN trench-gate MOSFETs with a-plane and m-plane sidewall channels. Applied Physics Express, 2016, 9, 121001.	1.1	49
47	Visible resonant modes in GaN-based photonic crystal membrane cavities. Applied Physics Letters, 2006, 88, 031111.	1.5	48
48	Growth and characterization of N-polar GaN films on SiC by metal organic chemical vapor deposition. Journal of Applied Physics, 2008, 104, .	1.1	48
49	Recessed Slant Gate AlGaN/GaN High Electron Mobility Transistors with 20.9 W/mm at 10 GHz. Japanese Journal of Applied Physics, 2007, 46, L1087.	0.8	47
50	High Linearity and High Gain Performance of N-Polar GaN MIS-HEMT at 30 GHz. IEEE Electron Device Letters, 2020, 41, 681-684.	2.2	46
51	Impact of strain on free-exciton resonance energies in wurtzite AlN. Journal of Applied Physics, 2007, 102, 123707.	1.1	44
52	Color-tunable <10â€‰<i> Î¼ </i>m square InGaN micro-LEDs on compliant GaN-on-porous-GaN pseudo-substrates. Applied Physics Letters, 2020, 117, .	1.5	44
53	Relaxed<i>c</i>-plane InGaN layers for the growth of strain-reduced InGaN quantum wells. Semiconductor Science and Technology, 2015, 30, 105015.	1.0	43
54	Effect of the Trimethylgallium Flow during Nucleation Layer Growth on the Properties of GaN Grown on Sapphire. Japanese Journal of Applied Physics, 1996, 35, L285-L288.	0.8	42

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55	Plasma Treatment for Leakage Reduction in AlGaN/GaN and GaN Schottky Contacts. IEEE Electron Device Letters, 2008, 29, 297-299.	2.2	42
56	Dispersion Free 450-V p GaN-Gated CAVETs With Mg-ion Implanted Blocking Layer. IEEE Electron Device Letters, 2017, 38, 933-936.	2.2	41
57	A comparative study of effects of SiNx deposition method on AlGaN/GaN heterostructure field-effect transistors. Applied Physics Letters, 2009, 94, .	1.5	40
58	Gallium Nitride Powders from Ammonolysis:Â Influence of Reaction Parameters on Structure and Properties. Chemistry of Materials, 2004, 16, 5088-5095.	3.2	39
59	Epitaxial Lateral Overgrowth of High Al Composition AlGaN Alloys on Deep Grooved SiC Substrates. Japanese Journal of Applied Physics, 2005, 44, L405-L407.	0.8	39
60	Impact of $hbox{CF}_{4}$ Plasma Treatment on GaN. IEEE Electron Device Letters, 2007, 28, 781-783.	2.2	39
61	N-Face Metalâ€"Insulatorâ€"Semiconductor High-Electron-Mobility Transistors With AlN Back-Barrier. IEEE Electron Device Letters, 2008, 29, 1101-1104.	2.2	39
62	Growth of strain-relaxed InGaN on micrometer-sized patterned compliant GaN pseudo-substrates. Applied Physics Letters, 2020, 116, .	1.5	38
63	First Demonstration of AlSiO as Gate Dielectric in GaN FETs; Applied to a High Performance OG-FET. IEEE Electron Device Letters, 2017, 38, 1575-1578.	2.2	37
64	Microwave Power Performance N-Polar GaN MISHEMTs Grown by MOCVD on SiC Substrates Using an $hbox{Al}_{2}hbox{O}_{3}$ Etch-Stop Technology. IEEE Electron Device Letters, 2012, 33, 44-46.	2.2	36
65	Demonstration of a GaN/AlGaN Superlattice-Based p-Channel FinFET With High ON-Current. IEEE Electron Device Letters, 2020, 41, 220-223.	2.2	36
66	Generation of coherent acoustic phonons in strained GaN thin films. Applied Physics Letters, 2001, 79, 3361-3363.	1.5	35
67	Ion versus pH sensitivity of ungated AlGaN/GaN heterostructure-based devices. Applied Physics Letters, 2010, 97, .	1.5	35
68	6.2 W/Mm and Record 33.8% PAE at 94 GHz From N-Polar GaN Deep Recess MIS-HEMTs With ALD Ru Gates. IEEE Microwave and Wireless Components Letters, 2021, 31, 748-751.	2.0	35
69	Optical Properties of InGaN/GaN Quantum Wells with Si Doped Barriers. Japanese Journal of Applied Physics, 1998, 37, L1362-L1364.	0.8	34
70	Capacitance-voltage characterization of interfaces between positive valence band offset dielectrics and wide bandgap semiconductors. Journal of Applied Physics, 2013, 114, .	1.1	34
71	Indium segregation in N-polar InGaN quantum wells evidenced by energy dispersive X-ray spectroscopy and atom probe tomography. Applied Physics Letters, 2017, 110, .	1.5	34
72	Two-Stage High-Gain High-Power Distributed Amplifier Using Dual-Gate GaN HEMTs. IEEE Transactions on Microwave Theory and Techniques, 2011, 59, 2059-2063.	2.9	33

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73	N-Polar GaN MIS-HEMTs on Sapphire With High Combination of Power Gain Cutoff Frequency and Three-Terminal Breakdown Voltage. IEEE Electron Device Letters, 2016, 37, 77-80.	2.2	33
74	Demonstration of GaN Current Aperture Vertical Electron Transistors With Aperture Region Formed by Ion Implantation. IEEE Transactions on Electron Devices, 2018, 65, 483-487.	1.6	33
75	Growth and properties of InGaN nanoscale islands on GaN. Journal of Crystal Growth, 1998, 189-190, 29-32.	0.7	32
76	Luminescence Characteristics of N-Polar GaN and InGaN Films Grown by Metal Organic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2009, 48, 071003.	0.8	31
77	Impact of Moisture and Fluorocarbon Passivation on the Current Collapse of AlGaN/GaN HEMTs. IEEE Electron Device Letters, 2012, 33, 1378-1380.	2.2	31
78	Model to explain the behavior of 2DEG mobility with respect to charge density in N-polar and Ga-polar AlGaN-GaN heterostructures. Journal of Applied Physics, 2016, 120, .	1.1	31
79	N-Polar GaN-on-Sapphire Deep Recess HEMTs With High W-Band Power Density. IEEE Electron Device Letters, 2020, 41, 1633-1636.	2.2	31
80	Growth and characterization of In-polar and N-polar InAlN by metal organic chemical vapor deposition. Journal of Applied Physics, 2010, 107, .	1.1	30
81	Fabrication of relaxed InGaN pseudo-substrates composed of micron-sized pattern arrays with high fill factors using porous GaN. Semiconductor Science and Technology, 2019, 34, 115020.	1.0	30
82	InGaN-Based microLED Devices Approaching 1% EQE with Red 609 nm Electroluminescence on Semi-Relaxed Substrates. Crystals, 2021, 11, 1364.	1.0	30
83	N-Polar InAlN/AlN/GaN MIS-HEMTs. IEEE Electron Device Letters, 2010, 31, 800-802.	2.2	29
84	N-Polar GaN MIS-HEMTs With a 12.1-W/mm Continuous-Wave Output Power Density at 4 GHz on Sapphire Substrate. IEEE Electron Device Letters, 2011, 32, 635-637.	2.2	29
85	Measurement of the hot electron mean free path and the momentum relaxation rate in GaN. Applied Physics Letters, 2014, 105, .	1.5	29
86	Electrical properties of N-polar AlGaN/GaN high electron mobility transistors grown on SiC by metalorganic chemical vapor deposition. Applied Physics Letters, 2009, 94, .	1.5	28
87	Engineering the (In, Al, Ga)N back-barrier to achieve high channel-conductivity for extremely scaled channel-thicknesses in N-polar GaN high-electron-mobility-transistors. Applied Physics Letters, 2014, 104, 092107.	1.5	26
88	N-Polar Deep Recess MISHEMTs With Record 2.9 W/mm at 94 GHz. IEEE Electron Device Letters, 2016, 37, 713-716.	2.2	25
89	Improved Dynamic R_{ON} of GaN Vertical Trench MOSFETs (OG-FETs) Using TMAH Wet Etch. IEEE Electron Device Letters, 2018, 39, 1030-1033.	2.2	25
90	Non-planar Selective Area Growth and Characterization of GaN and AlGaN. Japanese Journal of Applied Physics, 2003, 42, 6276-6283.	0.8	24

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91	Metalorganic Chemical Vapor Deposition Conditions for Efficient Silicon Doping in High Al-Composition AlGaN Films. Japanese Journal of Applied Physics, 2005, 44, 7227-7233.	0.8	24
92	High-Performance N-Face GaN Microwave MIS-HEMTs With > 70% Power-Added Efficiency. IEEE Electron Device Letters, 2009, 30, 802-804.	2.2	24
93	RF Performance of N-Polar AlGaN/GaN MIS-HEMTs Grown by MOCVD on Sapphire Substrate. IEEE Electron Device Letters, 2009, 30, 584-586.	2.2	24
94	Suppression of Mg propagation into subsequent layers grown by MOCVD. Journal of Applied Physics, 2017, 121, .	1.1	24
95	Milliwatt Power Deep Ultraviolet Light Emitting Diodes Grown on Silicon Carbide. Japanese Journal of Applied Physics, 2005, 44, L502-L504.	0.8	23
96	Growth of high purity N-polar (In,Ga)N films. Journal of Crystal Growth, 2017, 464, 127-131.	0.7	23
97	Observation of Hot Electron and Impact Ionization in N-Polar GaN MIS-HEMTs. IEEE Electron Device Letters, 2018, 39, 1007-1010.	2.2	23
98	Investigation of nitrogen polar p-type doped GaN/AlxGa(1-x)N superlattices for applications in wide-bandgap p-type field effect transistors. Applied Physics Letters, 2019, 115, .	1.5	23
99	An improved methodology for extracting interface state density at Si3N4/GaN. Applied Physics Letters, 2020, 116, .	1.5	23
100	Mapping piezoelectricâ€field distribution in gallium nitride with scanning secondâ€harmonic generation microscopy. Scanning, 2001, 23, 182-192.	0.7	22
101	Observation of positive thermal power coefficient in InGaN/GaN quantum well solar cells. Applied Physics Letters, 2011, 99, 071104.	1.5	22
102	Compliant Micron-Sized Patterned InGaN Pseudo-Substrates Utilizing Porous GaN. Materials, 2020, 13, 213.	1.3	22
103	Influence of AlN interlayer on the anisotropic electron mobility and the device characteristics of N-polar AlGaN/GaN metal-insulator-semiconductor-high electron mobility transistors grown on vicinal substrates. Journal of Applied Physics, 2010, 108, 074502.	1.1	21
104	Elimination of columnar microstructure in N-face InAlN, lattice-matched to GaN, grown by plasma-assisted molecular beam epitaxy in the N-rich regime. Applied Physics Letters, 2014, 104, .	1.5	21
105	Interfacial <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mrow><mml:mrow><mml:mi mathvariant="normal">N</mml:mi></mml:mrow></mml:mrow></mml:math> Vacancies in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mrow><mml:mi>Ga</mml:mi><mml:mi		

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109	AlGaN/AlN distributed bragg reflectors for deep ultraviolet wavelengths. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 1915-1919.	0.8	19
110	Very high channel conductivity in ultra-thin channel N-polar GaN/(AlN, InAlN, AlGaN) high electron mobility hetero-junctions grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2013, 102, 232104.	1.5	19
111	High frequency N-polar GaN planar MIS-HEMTs on sapphire with high breakdown and low dispersion. , 2016, , .		19
112	Study of interface barrier of SiNx/GaN interface for nitrogen-polar GaN based high electron mobility transistors. Journal of Applied Physics, 2008, 103, 124508.	1.1	18
113	N-Polar GaN/AlN MIS-HEMT With $f_{m MAX}$ of 204 GHz for Ka-Band Applications. IEEE Electron Device Letters, 2011, 32, 1683-1685.	2.2	18
114	Transport Studies of AlGaN/GaN Heterostructures of Different Al Mole Fractions With Variable $hbox{SiN}_{x}$ Passivation Stress. IEEE Transactions on Electron Devices, 2011, 58, 2589-2596.	1.6	18
115	Metal-organic chemical vapor deposition of high quality, high indium composition N-polar InGaN layers for tunnel devices. Journal of Applied Physics, 2017, 121, 185707.	1.1	18
116	Studies of carrier dynamics in unintentionally doped gallium nitride bandtail states. Applied Physics Letters, 2001, 78, 2724-2726.	1.5	17
117	Observation of huge nonlinear absorption enhancement near exciton resonance in GaN. Applied Physics Letters, 2003, 83, 3087-3089.	1.5	17
118	Characterizing the nanoacoustic superlattice in a phonon cavity using a piezoelectric single quantum well. Applied Physics Letters, 2006, 89, 143103.	1.5	17
119	Metalorganic Chemical Vapor Deposition Regrowth of InGaN and GaN on N-polar Pillar and Stripe Nanostructures. Japanese Journal of Applied Physics, 2007, 46, L230-L233.	0.8	17
120	Electron mobility in N-polar GaN/AlGaN/GaN heterostructuress. Applied Physics Letters, 2008, 93, .	1.5	17
121	f_{T} and $f_{m MAX}$ of 47 and 81 GHz , Respectively, on N-Polar GaN/AlN MIS-HEMT. IEEE Electron Device Letters, 2009, 30, 599-601.	2.2	17
122	Enhancement-Mode m-plane AlGaN/GaN Heterojunction Field-Effect Transistors with +3 V of Threshold Voltage Using Al$_{2}$O$_{3}$ Deposited by Atomic Layer Deposition. Applied Physics Express, 2011, 4, 096501.	1.1	17
123	Analysis of MOCVD SiNx Passivated N-Polar GaN MIS-HEMTs on Sapphire With High $f_{max}cdot V_{DS,Q}$. IEEE Electron Device Letters, 2018, 39, 409-412.	2.2	17
124	Metal-organic chemical vapor deposition of N-polar InN quantum dots and thin films on vicinal GaN. Journal of Applied Physics, 2018, 123, .	1.1	17
125	A Demonstration of Nitrogen Polar Gallium Nitride Current Aperture Vertical Electron Transistor. IEEE Electron Device Letters, 2019, 40, 885-888.	2.2	17
126	Stimulated emission and ultrafast carrier relaxation in InGaN multiple quantum wells. Applied Physics Letters, 2003, 82, 1416-1418.	1.5	16

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127	Local wing tilt analysis of laterally overgrown GaN by x-ray rocking curve imaging. Journal Physics D: Applied Physics, 2005, 38, A50-A54.	1.3	16
128	Correlation Between DCâ€“RF Dispersion and Gate Leakage in Deeply Recessed GaN/AlGaN/GaN HEMTs. IEEE Electron Device Letters, 2008, 29, 303-305.	2.2	16
129	RF Performance of Deep-Recessed N-Polar GaN MIS-HEMTs Using a Selective Etch Technology Without Ex Situ Surface Passivation. IEEE Electron Device Letters, 2011, 32, 134-136.	2.2	16
130	Optimization of a chlorine-based deep vertical etch of GaN demonstrating low damage and low roughness. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .	0.9	16
131	Compositionally graded InGaN layers grown on vicinal N-face GaN substrates by plasma-assisted molecular beam epitaxy. Journal of Crystal Growth, 2017, 465, 55-59.	0.7	16
132	First demonstration of improvement in hole conductivity in<i>c</i>-plane III-Nitrides through application of uniaxial strain. Japanese Journal of Applied Physics, 2019, 58, 030908.	0.8	16
133	Role of GaN cap layer for reference electrode free AlGaN/GaN-based pH sensors. Sensors and Actuators B: Chemical, 2019, 287, 250-257.	4.0	16
134	First demonstration of RF N-polar GaN MIS-HEMTs grown on bulk GaN using PAMBE. Semiconductor Science and Technology, 2019, 34, 045009.	1.0	16
135	Bias-Dependent Electron Velocity Extracted From N-Polar GaN Deep Recess HEMTs. IEEE Transactions on Electron Devices, 2020, 67, 1542-1546.	1.6	16
136	Large near resonance third order nonlinearity in GaN. Optical and Quantum Electronics, 2000, 32, 619-640.	1.5	15
137	GaNâ€based embedded 2D photonic crystal LEDs: Numerical optimization and device characterization. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S675.	0.8	15
138	Lateral confinement of electrons in vicinal N-polar AlGaN/GaN heterostructure. Applied Physics Letters, 2010, 97, 162106.	1.5	15
139	Plasma-assisted molecular beam epitaxy growth diagram of InGaN on (0001)GaN for the optimized synthesis of InGaN compositional grades. Physica Status Solidi (B): Basic Research, 2016, 253, 626-629.	0.7	15
140	Net negative fixed interface charge for Si3N4 and SiO2 grown in situ on 000-1 N-polar GaN. Applied Physics Letters, 2019, 115, 032103.	1.5	15
141	Method of growing elastically relaxed crack-free AlGaN on GaN as substrates for ultra-wide bandgap devices using porous GaN. Applied Physics Letters, 2020, 117, .	1.5	15
142	Observation of I_D-V_D Kink in N-Polar GaN MIS-HEMTs at Cryogenic Temperatures. IEEE Electron Device Letters, 2020, 41, 345-348.	2.2	15
143	Evaluation of linearity at 30 GHz for N-polar GaN deep recess transistors with 10.3 W/mm of output power and 47.4% PAE. Applied Physics Letters, 2021, 119, .	1.5	15
144	Electrical and structural properties of AlGaN/AlGaN superlattice structures grown by metal-organic chemical vapor deposition. Optical Materials, 2003, 23, 187-195.	1.7	14

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145	Simultaneous four-photon luminescence, third-harmonic generation, and second-harmonic generation microscopy of GaN. Optics Letters, 2005, 30, 2463.	1.7	14
146	Self-Aligned Technology for N-Polar GaN/Al(Ga)N MIS-HEMTs. IEEE Electron Device Letters, 2011, 32, 33-35.	2.2	14
147	Controlled low Si doping and high breakdown voltages in GaN on sapphire grown by MOCVD. Semiconductor Science and Technology, 2016, 31, 125018.	1.0	14
148	Digital growth of thick N-polar InGaN films on relaxed InGaN pseudosubstrates. Applied Physics Express, 2017, 10, 111001.	1.1	14
149	Infrared luminescence from N-polar InN quantum dots and thin films grown by metal organic chemical vapor deposition. Applied Physics Letters, 2019, 114, 241103.	1.5	14
150	Femtosecond dynamics of exciton bleaching in bulk GaN at room temperature. Applied Physics Letters, 2002, 81, 85-87.	1.5	13
151	Ultrashort hole capture time in Mg-doped GaN thin films. Applied Physics Letters, 2002, 81, 3975-3977.	1.5	13
152	Low Ohmic Contact Resistance<i>m</i>-Plane AlGaN/GaN Heterojunction Field-Effect Transistors with Enhancement-Mode Operations. Applied Physics Express, 2010, 3, 101002.	1.1	13
153	Method to Predict and Optimize Charge Sensitivity of Ungated AlGaN/GaN HEMT-Based Ion Sensor Without Use of Reference Electrode. IEEE Sensors Journal, 2015, 15, 5320-5326.	2.4	13
154	InGaN lattice constant engineering via growth on (In,Ga)N/GaN nanostripe arrays. Semiconductor Science and Technology, 2015, 30, 105020.	1.0	13
155	Crystal quality and growth evolution of aluminum nitride on silicon carbide. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 1708-1711.	0.8	12
156	A donor-like trap at the InGaN/GaN interface with net negative polarization and its possible consequence on internal quantum efficiency. Semiconductor Science and Technology, 2013, 28, 105021.	1.0	12
157	Performance projection of IIIâ€nitride heterojunction nanowire tunneling fieldâ€effect transistors. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 905-908.	0.8	12
158	Growth of N-polar GaN by ammonia molecular beam epitaxy. Journal of Crystal Growth, 2018, 481, 65-70.	0.7	12
159	Proposed existence of acceptor-like traps at positive polarization interfaces in p-type III-nitride semiconductors. Applied Physics Letters, 2020, 117, .	1.5	12
160	Ultra-high silicon doped N-polar GaN contact layers grown by metal-organic chemical vapor deposition. Semiconductor Science and Technology, 2020, 35, 095002.	1.0	12
161	Study of the n⁺ GaN Cap in AlGaN/GaN High Electron Mobility Transistors with Reduced Sourceâ€"Drain Resistance. Japanese Journal of Applied Physics, 2007, 46, L842.	0.8	11
162	Design of polarization-dipole-induced isotype heterojunction diodes for use in IIIâ€"N hot electron transistors. Applied Physics Express, 2014, 7, 014102.	1.1	11

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